

FDS3570

80V N-Channel PowerTrench™ MOSFET

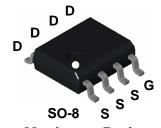
General Description

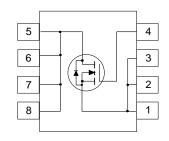
This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\scriptscriptstyle DS(\rm on)}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

Features

- 9 A, 80 V. $R_{DS(ON)} = 0.019 \Omega$ @ $V_{GS} = 10 V$ $R_{DS(ON)} = 0.022 \Omega$ @ $V_{GS} = 6 V$.
- Fast switching speed.
- High performance trench technology for extremely low $\mathbf{R}_{\text{\tiny DS(ON)}}.$
- High power and current handling capability.





Absolute Maximum Ratings T_a = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage	80	V	
V _{GSS}	Gate-Source Voltage		±20	V
I_D	Drain Current - Continuous	(Note 1a)	9	А
	- Pulsed		50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T _J , T _{stg}	Operating and Storage Junction Temperature	-55 to +150	°C	

Thermal Characteristics

R _e JA	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
Raic	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

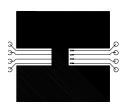
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity	
FDS3570	FDS3570	13"	12mm	2500 units	

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	80			V
<u>A</u> BVdss ΛΤυ	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		77		mV/∘C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 64 V, V _{GS} = 0 V			1	μΑ
GSSF	Gate-Body Leakage Current Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
GSSR	Gate-Body Leakage Current Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.4	4	V
∆VGS(th) ∧T,j	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-7		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 6 \text{ V}, I_D = 8.4 \text{ A}$		0.015 0.027 0.016	0.019 0.038 0.022	Ω
D(on)	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	25			Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 7.6 \text{ A}$		40		S
Dynamic	: Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		2750		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		280		pF
C _{rss}	Reverse Transfer Capacitance	1		140		pF
Switchin	g Characteristics (Note 2)			•	•	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 40 \text{ V}, I_{D} = 1 \text{ A},$		20	32	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		12	24	ns
d(off)	Turn-Off Delay Time			60	95	ns
f	Turn-Off Fall Time			24	38	ns
Q_g	Total Gate Charge	$V_{DS} = 40 \text{ V}, I_{D} = 9 \text{ A},$		54	76	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V		9.6		nC
Q_{gd}	Gate-Drain Charge			14		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings				
I _S	Maximum Continuous Drain-Source				2.1	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.1 \text{ A}$ (Note 2)		0.72	1.2	V

^{1.} R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50° C/W when mounted on a 1 in² pad of 2 oz. copper.





b) 105° C/W when mounted on a 0.04 in² pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

Typical Characteristics

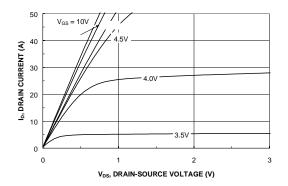


Figure 1. On-Region Characteristics.

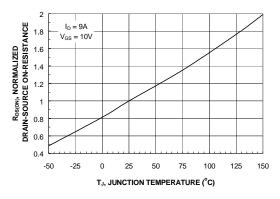


Figure 3. On-Resistance Variation with Temperature.

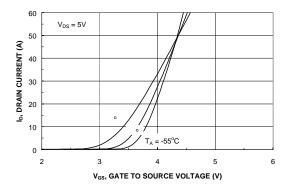


Figure 5. Transfer Characteristics.

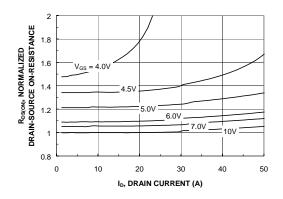


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

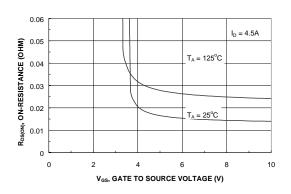


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

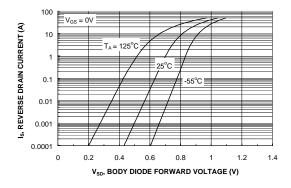
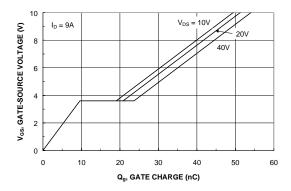


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



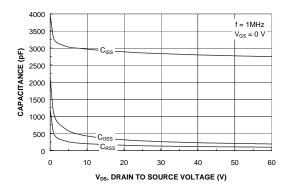
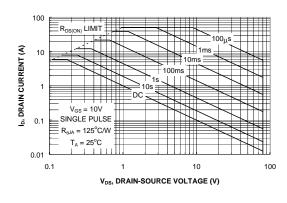


Figure 7. Gate-Charge Characteristics.





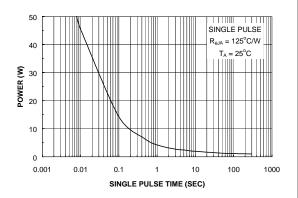


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

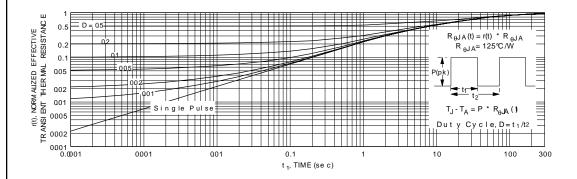
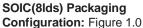


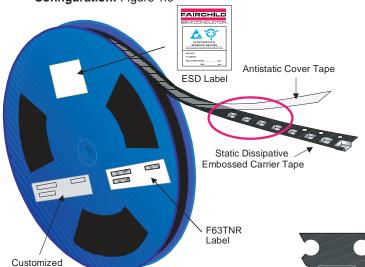
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

SO-8 Tape and Reel Data and Package Dimensions





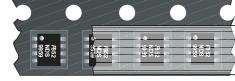


Packaging Description:

Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and amit-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 300cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (antistatic coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

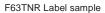
These full reles are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.





SOIC (8lds) Packaging Information Packaging Option Standard o flow code) L86Z D84Z Rail/Tube TNR Packaging type TNR TNR Qty per Reel/Tube/Bag 2.500 4.000 500 Reel Size 13" Dia 13" Dia 7" Dia Box Dimension (mm) 343y64y343 530x130x83 343y64y343 184v187v47 Max qty per Box 5,000 30,000 8,000 1,000 Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

SOIC-8 Unit Orientation



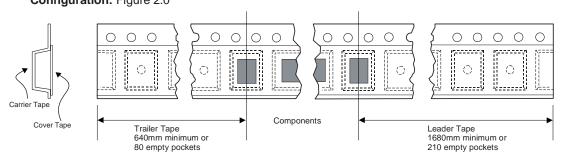
Label



F63TNLabel F63TN Label F63TN Label

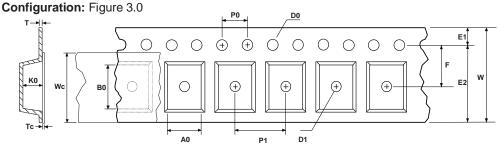
343mm x 342mm x 64mm

SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0





SOIC(8lds) Embossed Carrier Tape



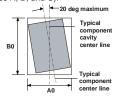


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

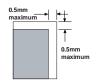


Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

Component Rotation



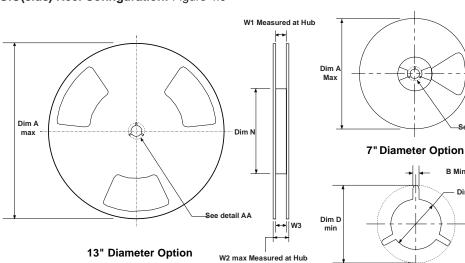
Sketch C (Top View)

Component lateral movement

Dim C

DETAIL AA

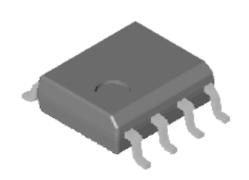
SOIC(8lds) Reel Configuration: Figure 4.0

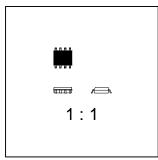


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SO-8 Tape and Reel Data and Package Dimensions, continued

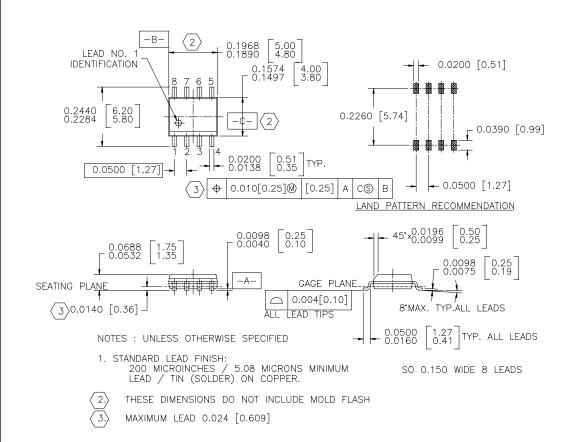
SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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 E^2CMOS^{TM} PowerTrenchTM

FACT™ QFET™ FACT Quiet Series™ QS™

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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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